Abstracts

L-Band Internally Matched Si-MMIC Low Noise Amplifier

N. Suematsu, M. Ono, S. Kubo, H. Sato, Y. Iyama and O. Ishida. "L-Band Internally Matched Si-MMIC Low Noise Amplifier." 1996 MTT-S International Microwave Symposium Digest 96.3 (1996 Vol. III [MWSYM]): 1225-1228.

A Si-MMIC low noise amplifier (LNA), fabricated in conventional 0.8um Bi-CMOS process, was developed. This LNA is monolithically integrated on a low resistive Si substrate with coplanar waveguide (CPW) type matching circuits. At 1.9GHz, noise figure of 2.7dB and gain of 10dB were obtained at 2V / 2mA d.c.supply.

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